

# 2SK1406

## Silicon N-Channel Power F-MOS

### ■ Features

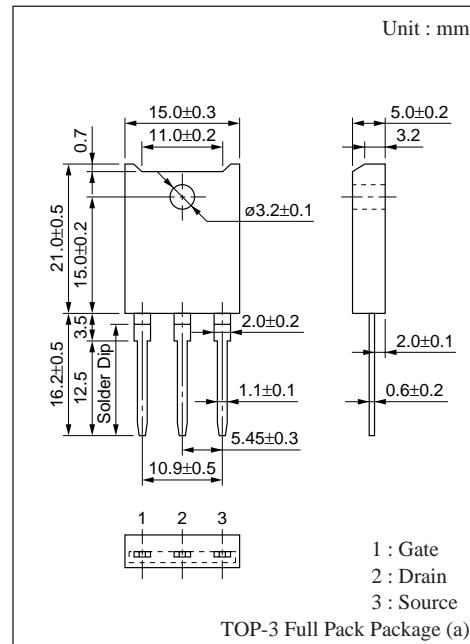
- Low ON-resistance  $R_{DS(on)}$  :  $R_{DS(on)} = 0.32\Omega$ (typ)
- High-speed switching :  $t_f = 140\text{ns}$ (typ)
- No secondary breakdown
- High breakdown voltage, large allowable power dissipation

### ■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

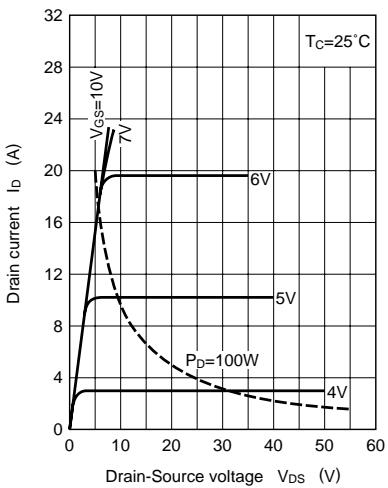
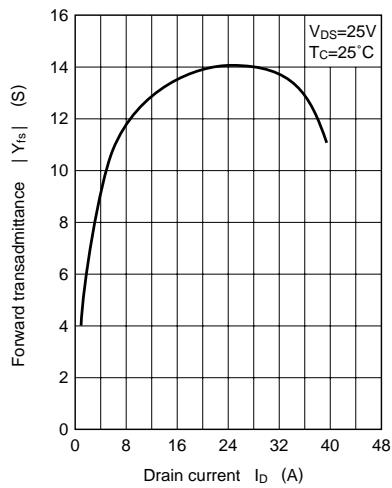
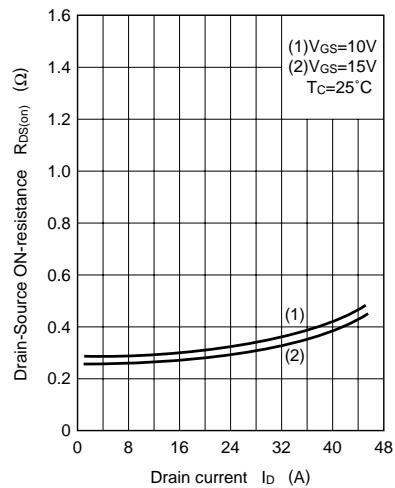
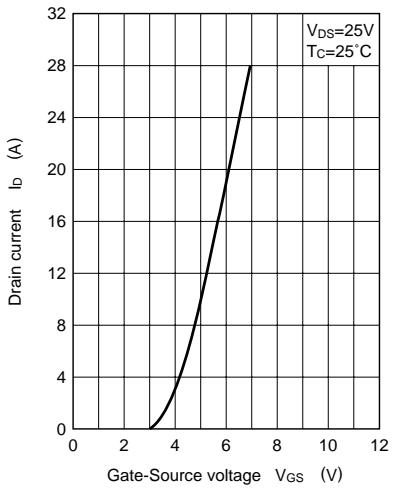
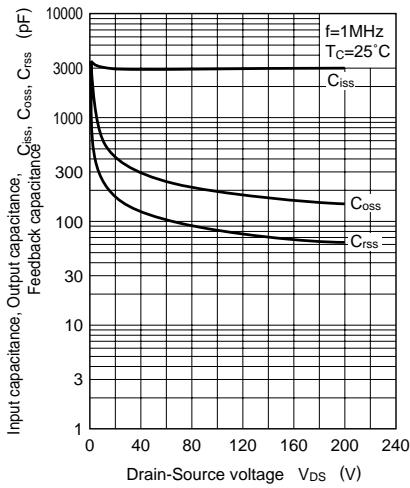
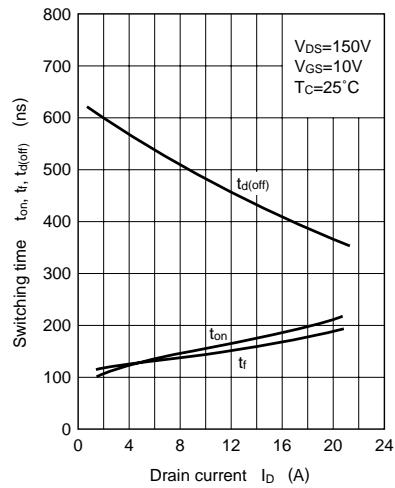
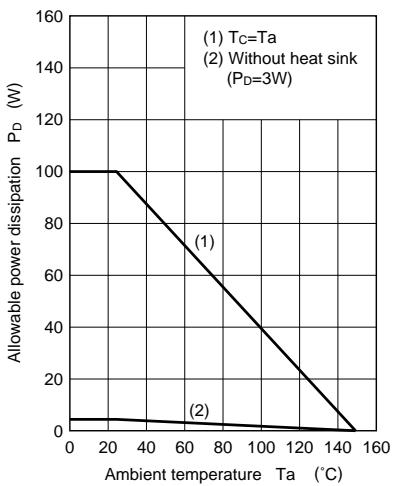
### ■ Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	$V_{DSS}$	500	V
Gate-Source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC $I_D$	$\pm 20$	A
	Pulse $I_{DP}$	$\pm 40$	A
Allowable power dissipation	$T_c = 25^\circ\text{C}$	$P_D$	W
	$T_a = 25^\circ\text{C}$		
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

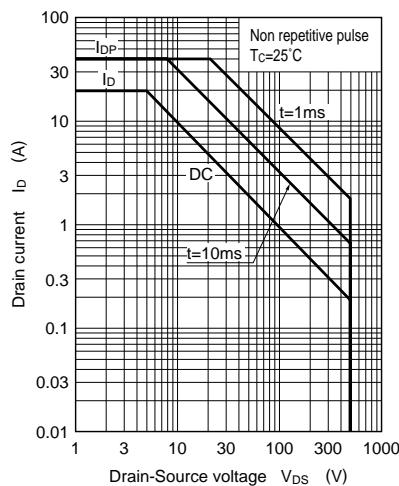


### ■ Electrical Characteristics ( $T_c = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	$I_{DSS}$	$V_{DS} = 400\text{V}, V_{GS} = 0$			0.1	mA
Gate-Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$			$\pm 1$	$\mu\text{A}$
Drain-Source breakdown voltage	$V_{DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	500			V
Gate threshold voltage	$V_{th}$	$V_{DS} = 25\text{V}, I_D = 1\text{mA}$	1		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 10\text{A}$		0.32	0.4	$\Omega$
Drain-Source on voltage	$V_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$			9	V
Forward transadmittance	$ Y_{fs} $	$V_{DS} = 25\text{V}, I_D = 10\text{A}$	7.2	12		S
Input capacitance	$C_{iss}$	$V_{DS} = 20\text{V}, V_{GS} = 0, f = 1\text{MHz}$		3000		pF
Output capacitance	$C_{oss}$			430		pF
Feedback capacitance	$C_{rss}$			175		pF
Turn-on time	$t_{on}$	$V_{GS} = 10\text{V}, I_D = 10\text{A}$ $V_{DS} = 150\text{V}, R_L = 15\Omega$		150		ns
Fall time	$t_f$			140		ns
Turn-off time (delay time)	$t_{d(off)}$			480		ns

$I_D - V_{DS}$  $|Y_{fs}| - I_D$  $R_{DS(on)} - I_D$  $I_D - V_{GS}$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $t_{on}, t_f, t_d(\text{off}) - I_D$  $P_D - Ta$ 

Area of safe operation (ASO)

 $R_{DS(on)} - I_D$ 